TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1451A

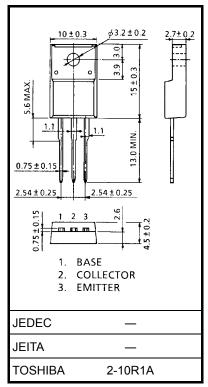
High-Speed, High-Current Switching Applications

Unit: mm

- Low collector saturation voltage
 - $V_{CE (sat)} = -0.4 \text{ V (max) (IC} = -6 \text{ A)}$
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)
- Complementary to 2SC3709A

Absolute Maximum Ratings (Tc = 25°C)

| Characteristics | Symbol | Rating | Unit | |
|-----------------------------|------------------|------------|------|--|
| Collector-base voltage | V _{CBO} | -60 | V | |
| Collector-emitter voltage | V _{CEO} | -50 | V | |
| Emitter-base voltage | V _{EBO} | -6 | V | |
| Collector current | IC | -12 | Α | |
| Base current | ΙΒ | -2 | Α | |
| Collector power dissipation | D. | 30 | W | |
| (Tc = 25°C) | PC | 30 | VV | |
| Junction temperature | Tj | 150 | °C | |
| Storage temperature range | T _{stg} | -55 to 150 | °C | |



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

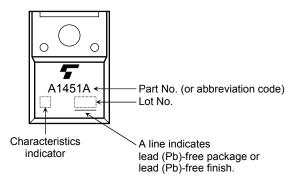


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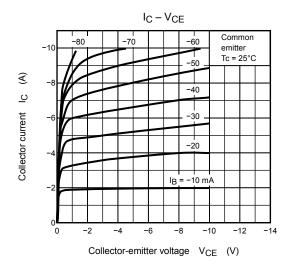
| Chara | acteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|----------------------|--------------------|----------------------------|--|-----|-------|------|------|
| Collector cut-off of | current | I _{CBO} | V _{CB} = -60 V, I _E = 0 | _ | _ | -10 | μΑ |
| Emitter cut-off cu | rrent | I _{EBO} | V _{EB} = -6 V, I _C = 0 | _ | _ | -10 | μΑ |
| Collector-emitter | breakdown voltage | V (BR) CEO | I _C = -50 mA, I _B = 0 | -50 | _ | _ | V |
| DC current gain | | h _{FE (1)} (Note) | V _{CE} = -1 V, I _C = -1 A | 70 | _ | 240 | |
| | | h _{FE (2)} | V _{CE} = -1 V, I _C = -6 A | 40 | _ | _ | |
| Collector-emitter | saturation voltage | V _{CE (sat)} | I _C = -6 A, I _B = -0.3 A | _ | -0.15 | -0.4 | V |
| Base-emitter satu | ıration voltage | V _{BE (sat)} | I _C = -6 A, I _B = -0.3 A | _ | -0.9 | -1.2 | V |
| Transition freque | ncy | f _T | V _{CE} = -5 V, I _C = -1 A | _ | 70 | _ | MHz |
| Collector output of | capacitance | C _{ob} | V _{CB} = -10 V, I _E = 0, f = 1 MHz | _ | 320 | _ | pF |
| | Turn-on time | t _{on} | Output 20 μs Input B2 | _ | 0.3 | _ | |
| | Storage time | t _{stg} | 20 μs Input B2 Output BB2 Output BB1 B1 | _ | 1.0 | | μs |
| | Fall time | t _f | $V_{CC} \approx -30 \text{ V}$ $-I_{B1} = I_{B2} = 0.3 \text{ A, duty cycle} ≤ 1%$ | _ | 0.2 | _ | |

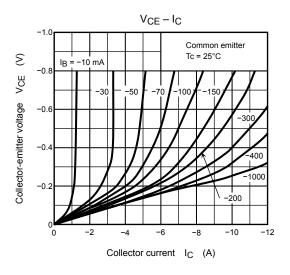
Note: $h_{FE(1)}$ classification O: 70 to 140, Y: 120 to 240

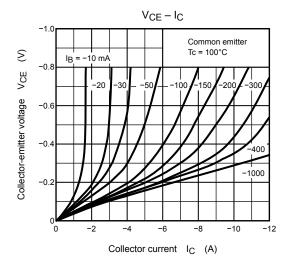
Marking

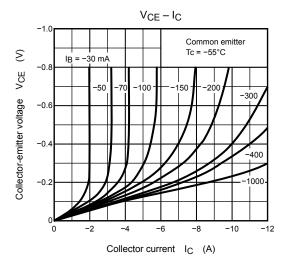


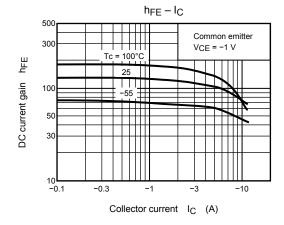
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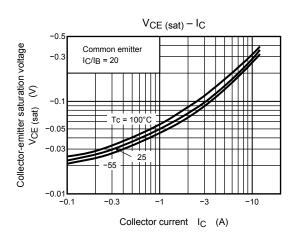




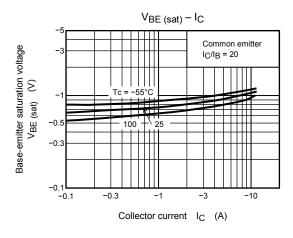


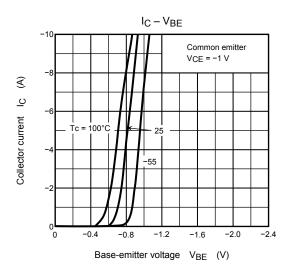


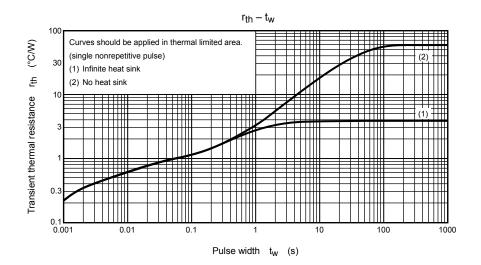


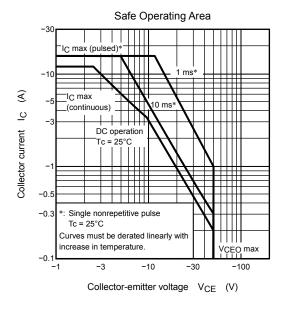


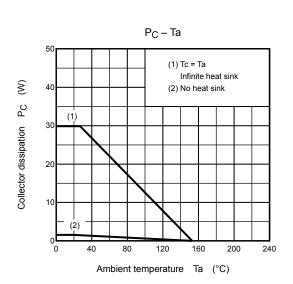
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